

L Number	Hits	Search Text	DB	Time stamp
-	136905	((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)	USPAT; US-PGPUB	2004/08/05 15:19
-	115095	((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)	USPAT; US-PGPUB	2004/08/05 15:20
-	14226	((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)	USPAT; US-PGPUB	2004/08/05 15:20
-	8567	(((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)	USPAT; US-PGPUB	2004/08/05 15:21
-	1983	((((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer	USPAT; US-PGPUB	2004/08/05 15:21
-	1224	((((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer) and ((polysilicon silicon polycide) near15 spacer)	USPAT; US-PGPUB	2004/08/05 15:19
-	60905	((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)	EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:19
-	1268	((((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer) and ((polysilicon silicon polycide) with spacer)	USPAT; US-PGPUB	2004/08/05 15:19
-	7846	((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)	EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:20
-	1367	((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)	EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:21
-	1160	(((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)	EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:21
-	148	((((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer	EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:21